

128MB DDR SDRAM MODULE

(16Mx64(8Mx16*2Bank) based on 8Mx16 DDR SDRAM)

Unbuffered 184pin DIMM
64-bit Non-ECC/Parity

Revision 0.0

Aug. 1999

Revision History**Revision 0 (Aug 1998)**

1. First release for internal usage

Revision 0.1 (May. 1999)

1. Changed die revision from B-die to C-die
2. Changed DC/AC characteristics item from old version

Revision 0.2 (Aug. 1999)

1. Changed die revision from C-die to B-die
2. Modified binning policy

From	To
-Z (133Mhz)	-Z (133Mhz/266Mbps@CL=2)
-8 (125Mhz)	-Y (133Mhz/266Mbps@CL=2.5)
-0 (100Mhz)	-0 (100Mhz/200Mbps@CL=2)

3. Modified the following AC spec values

	From.		To.		
	-Z	-0	-Z	-Y	-0
tAC	+/- 0.75ns	+/- 1ns	+/- 0.75ns	+/- 0.75ns	+/- 0.8ns
tDQSCK	+/- 0.75ns	+/- 1ns	+/- 0.75ns	+/- 0.75ns	+/- 0.8ns
tDQSQ	+/- 0.5ns	+/- 0.75ns	+/- 0.5ns	+/- 0.5ns	+/- 0.6ns
tDS/tDH	0.5 ns	0.75 ns	0.5 ns	0.5 ns	0.6 ns
tCDLR ^{*1}	2.5tCK-tDQSS	2.5tCK-tDQSS	1tCK	1tCK	1tCK
tPRE ^{*1}	1tCK +/- 0.75ns	1tCK +/- 1ns	0.9/1.1 tCK	0.9/1.1 tCK	0.9/1.1 tCK
tRPST ^{*1}	tCK/2 +/- 0.75ns	tCK/2 +/- 1ns	0.4/0.6 tCK	0.4/0.6 tCK	0.4/0.6 tCK
tHZQ ^{*1}	tCK/2 +/- 0.75ns	tCK/2 +/- 1ns	+/- 0.75ns	+/- 0.75ns	+/-0.8ns

^{*1} : Changed description method for the same functionality. This means no difference from the previous version.

4. Changed the following AC parameter symbol From tDQCK To tAC
Output data access time from CK/CK

KMM368L1714BT

184pin Unbuffered DDR SDRAM MODULE

Preliminary

KMM368L1714BT DDR SDRAM 184pin DIMM

16Mx64 DDR SDRAM 184pin DIMM based on 8Mx16

1. GENERAL DESCRIPTION

The Samsung KMM368L1714BT is 16M bit x 64 Double Data Rate SDRAM high density memory modules based on first gen of 128Mb DDR SDRAM respectively.

The Samsung KMM368L1714BT consists of eight CMOS 8M x 16 bit with 4banks Double Data Rate SDRAMs in 66pin TSOP-II(400mil) packages mounted on a 184pin glass-epoxy substrate. Four 0.1uF decoupling capacitors are mounted on the printed circuit board in parallel for each DDR SDRAM.

The KMM368L1714BT is Dual In-line Memory Modules and intended for mounting into 184pin edge connector sockets.

Synchronous design allows precise cycle control with the use of system clock. Data I/O transactions are possible on both edges of DQS. Range of operating frequencies, programmable latencies and burst lengths allow the same device to be useful for a variety of high bandwidth, high performance memory system applications.

2. FEATURE

- Performance range

Part No.	Max Freq.	Interface
KMM368L1714BT-G(F)Z	133MHz(7.5ns@CL=2)	SSTL_2
KMM368L1714BT-G(F)Y	133MHz(7.5ns@CL=2.5)	
KMM368L1714BT-G(F)0	100MHz(10ns@CL=2)	

- Power supply
Vdd: 2.5V ± 0.2V
Power: G - normal, F - Low power
- MRS cycle with address key programs
CAS Latency (Access from column address):2,2.5
Burst length ;2, 4, 8
Data scramble ;Sequential & Interleave
- Serial presence detect with EEPROM
- PCB : **Height 1450 (mil)**, double sided component

3. PIN CONFIGURATIONS (Front side/back side)

Pin	Front	Pin	Front	Pin	Front	Pin	Back	Pin	Back	Pin	Back
1	VREF	32	A5	62	VDDQ	93	VSS	124	VSS	154	/RAS
2	DQ0	33	DQ24	63	/WE	94	DQ4	125	A6	155	DQ45
3	VSS	34	VSS	64	DQ41	95	DQ5	126	DQ28	156	VDDQ
4	DQ1	35	DQ25	65	/CAS	96	VDDQ	127	DQ29	157	/CS0
5	DQS0	36	DQS3	66	VSS	97	DM0	128	VDDQ	158	/CS1
6	DQ2	37	A4	67	DQS5	98	DQ6	129	DM3	159	DM5
7	VDD	38	VDD	68	DQ42	99	DQ7	130	A3	160	VSS
8	DQ3	39	DQ26	69	DQ43	100	VSS	131	DQ30	161	DQ46
9	NC	40	DQ27	70	VDD	101	NC	132	VSS	162	DQ47
10	NC	41	A2	71	NC	102	NC	133	DQ31	163	NC
11	VSS	42	VSS	72	DQ48	103	*A13	134	*CB4	164	VDDQ
12	DQ8	43	A1	73	DQ49	104	VDDQ	135	*CB5	165	DQ52
13	DQ9	44	*CB0	74	VSS	105	DQ12	136	VDDQ	166	DQ53
14	DQS1	45	*CB1	75	/CK2	106	DQ13	137	*CK1	167	NC
15	VDDQ	46	VDD	76	CK2	107	DM1	138	*CK1	168	VDD
16	CK0	47	*DQS8	77	VDDQ	108	VDD	139	VSS	169	DM6
17	/CK0	48	A0	78	DQS6	109	DQ14	140	*DM8	170	DQ54
18	VSS	49	*CB2	79	DQ50	110	DQ15	141	A10	171	DQ55
19	DQ10	50	VSS	80	DQ51	111	CKE1	142	*CB6	172	VDDQ
20	DQ11	51	*CB3	81	VSS	112	VDDQ	143	VDDQ	173	NC
21	CKE0	52	BA1	82	VDDID	113	*BA2	144	*CB7	174	DQ60
22	VDDQ	KEY		83	DQ56	114	DQ20	KEY		175	DQ61
23	DQ16	53	DQ32	84	DQ57	115	*A12	145	VSS	176	VSS
24	DQ17	54	VDDQ	85	VDD	116	VSS	146	DQ36	177	DM7
25	DQS2	55	DQ33	86	DQS7	117	DQ21	147	DQ37	178	DQ62
26	VSS	56	DQS4	87	DQ58	118	A11	148	VDD	179	DQ63
27	A9	57	DQ34	88	DQ59	119	DM2	149	DM4	180	VDDQ
28	DQ18	58	VSS	89	VSS	120	VDD	150	DQ38	181	SA0
29	A7	59	BA0	90	WP	121	DQ22	151	DQ39	182	SA1
30	VDDQ	60	DQ35	91	SDA	122	A8	152	VSS	183	SA2
31	DQ19	61	DQ40	92	SCL	123	DQ23	153	DQ44	184	V33

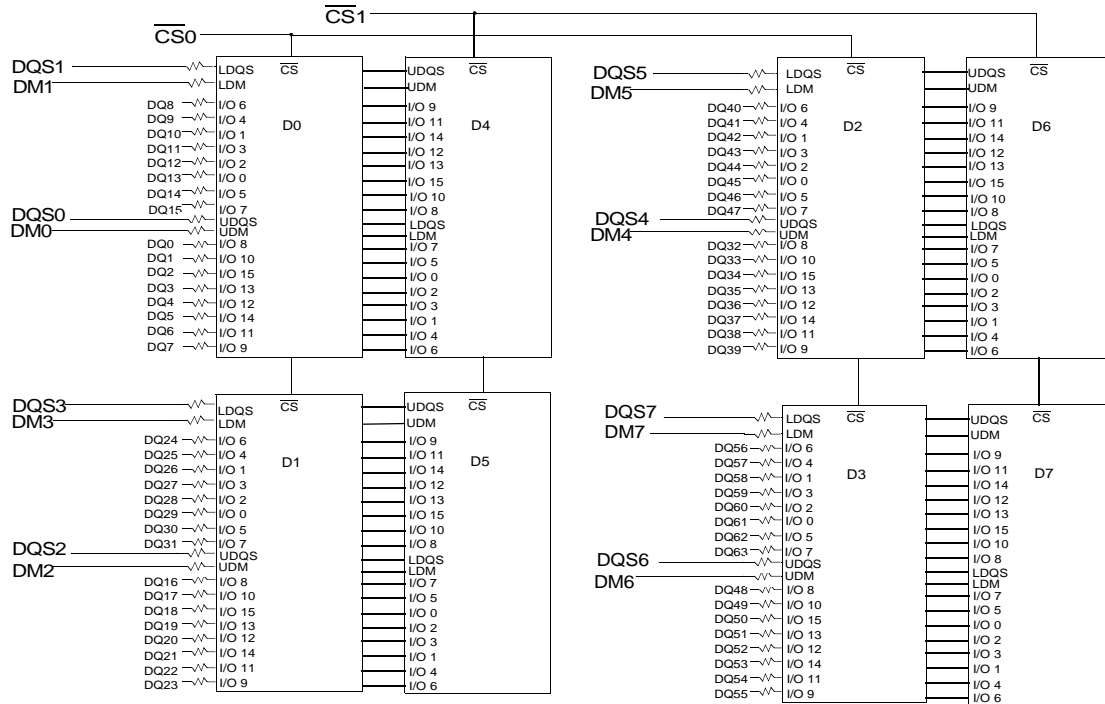
4. PIN DESCRIPTION

Pin Name	Function
A0 ~ A11	Address input (Multiplexed)
BA0 ~ BA1	Bank Select Address
DQ0 ~ DQ63	Data input/output
DQS0 ~ DQS7	Data Strobe input/output
CK0,CK0 , CK2, CK2	Clock input
CKE0,CKE1	Clock enable input
CS0, CS1	Chip select input
RAS	Row address strobe
CAS	Column address strobe
WE	Write enable
DM0 ~ DM7	Data - in mask
VDD	Power supply (2.5V)
VDDQ	Power Supply for DQs(2.5V)
VSS	Ground
VREF	Power supply for reference
V33	Serial EEPROM Power Supply (3.3V)
SDA	Serial data I/O
SCL	Serial clock
SA0 ~ 2	Address in EEPROM
WP	Write protection
VDDID	VDD identification flag
DU	Don't use
NC	No connection

* These pins are not used in this module.

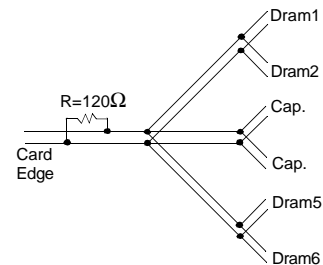
SAMSUNG ELECTRONICS CO., Ltd. reserves the right to change products and specifications without notice.

5. Functional Block Diagram



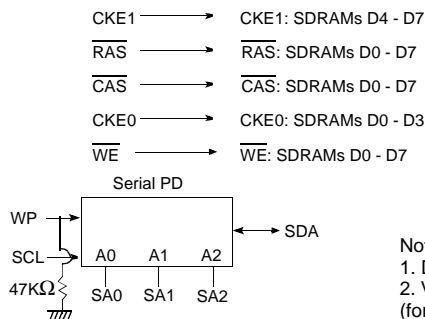
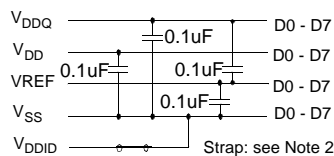
Clock Wiring	
Clock Input	SDRAMs
CK0/CK0	4 SDRAMs
CK1/CK1	NC
CK2/CK2	4 SDRAMs

*Clock Net Wiring



BA0 - BAN → BA0-BAN: DDR SDRAMs D0 - D7

A0 - AN → A0-AN: DDR SDRAMs D0 - D7



Notes:

1. DQ, DQS, DM/DQS resistors: 22 Ohms.
2. VDDID strap connections (for memory device VDD, VDDQ):
STRAP OUT (OPEN): VDD = VDDQ
STRAP IN (VSS): VDD ≠ VDDQ.

6. ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Voltage on any pin relative to Vss	V _{IN} , V _{OUT}	-0.5 ~ 3.6	V
Voltage on VDD supply relative to Vss	VDD	-1.0 ~ 4.6	V
Voltage on VDDQ supply relative to Vss	VDDQ	-0.5 ~ 3.6	V
Storage temperature	T _{STG}	-55 ~ +150	°C
Power dissipation	P _D	8	W
Short circuit current	I _{OS}	50	mA

Note : Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded.
 Functional operation should be restricted to recommended operating condition.
 Exposure to higher than recommended voltage for extended periods of time could affect device reliability.

7. POWER & DC OPERATING CONDITIONS (SSTL_2 In/Out)

Recommended operating conditions(Voltage referenced to Vss=0V, T_A=0 to 70°C)

Parameter	Symbol	Min	Max	Unit	Note
Supply voltage(for device with a nominal VDD of 2.5V)	VDD	2.3	2.7	V	
I/O Supply voltage	VDDQ	2.3	2.7	V	
I/O Reference voltage	VREF	1.15	1.35	V	1
I/O Termination voltage(system)	V _{TT}	VREF-0.04	VREF+0.04	V	2
Input logic high voltage	V _{IH} (DC)	VREF+0.18	VDDQ+0.3	V	
Input logic low voltage	V _{IL} (DC)	-0.3	VREF-0.18	V	
Input Voltage Level, CK and $\overline{\text{CK}}$ inputs	V _{IN} (DC)	-0.3	VDDQ+0.3	V	
Input Differential Voltage, CK and $\overline{\text{CK}}$ inputs	V _{ID} (DC)	0.36	VDDQ+0.6	V	
Input leakage current	I _I	-5	5	uA	3
Output leakage current	I _{OZ}	-5	5	uA	
Output High Current (V _{OUT} = 1.95V)	I _{OH}	-15.2		mA	
Output Low Current (V _{OUT} = 0.35V)	I _{OL}	15.2		mA	

Note : 1. Typically, the value of VREF is expected to be about 0.5*VDDQ of the transmitting device.
 VREF is expected to track variation in VDDQ.
 2. Peak to peak AC noise on VREF may not exceed 2% VREF(DC).
 3. V_{tt} of the transmitting device must track VREF of the receiving device.

8. DC CHARACTERISTICSRecommended operating conditions Unless Otherwise Noted, $T_A=0$ to 70°C

Parameter	Symbol	Test Condition	CAS Latency	Version			Unit	Note
				-Z	-Y	-0		
Operating Current (One Bank Active)	IDD1	Burst=2 $t_{RC}=t_{RC}(\text{min})$, $CL=2.5$ $I_{OUT}=0\text{mA}$, Active-Read-Precharge		T.B.D	T.B.D	T.B.D	mA	1
Precharge Power-down Standby Current	IDD2P	$CKE \leq V_{IL}(\text{max})$, $t_{CK}=t_{CK}(\text{min})$, All banks idle		T.B.D			mA	
Precharge Standby Current in Non Power-down mode	IDD2N	$CKE \geq V_{IH}(\text{min})$, $\overline{CS} \geq V_{IH}(\text{min})$, $t_{CK}=t_{CK}(\text{min})$		T.B.D			mA	
Active Standby Current in Power-down mode	IDD3P	All banks idle, $CKE \leq V_{IL}(\text{max})$, $t_{CK}=t_{CK}(\text{min})$		T.B.D			mA	
Active Standby Current in Non Power-down mode	IDD3N	One bank; Active-Precharge, $t_{RC}=t_{RAS}(\text{max})$, $t_{CK}=t_{CK}(\text{min})$		T.B.D			mA	
Operating Current(Read)	IDD4R	Burst=2, $t_{CK}=t_{CK}(\text{min})$, $I_{OUT}=0\text{mA}$	2.5	T.B.D	T.B.D	T.B.D	mA	1
			2	T.B.D	T.B.D	T.B.D		
Operating Current(Write)	IDD4W	Burst=2, $t_{CK}=t_{CK}(\text{min})$	2.5	T.B.D	T.B.D	T.B.D	mA	1
			2	T.B.D	T.B.D	T.B.D		
Auto Refresh Current	IDD5	$t_{RC} \geq t_{RFC}(\text{min})$		T.B.D			mA	2
Self Refresh Current	IDD6	$CKE \leq 0.2\text{V}$		T.B.D			mA	

Note : 1. Measured with outputs open.

2. Refresh period is 64ms

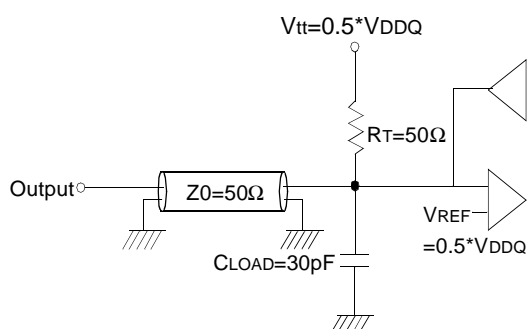
9. AC Operating Conditions

Parameter/Condition	Symbol	Min	Max	Unit	Note
Input High (Logic 1) Voltage, DQ, DQS and DM signals	$V_{IH}(\text{AC})$	$V_{REF} + 0.35$		V	
Input Low (Logic 0) Voltage, DQ, DQS and DM signals.	$V_{IL}(\text{AC})$		$V_{REF} - 0.35$	V	
Input Differential Voltage, CK and CK inputs	$V_{ID}(\text{AC})$	0.7	$V_{DDQ}+0.6$	V	1
Input Crossing Point Voltage, CK and CK inputs	$V_{IX}(\text{AC})$	$0.5 \cdot V_{DDQ}-0.2$	$0.5 \cdot V_{DDQ}+0.2$	V	2

Note 1. V_{ID} is the magnitude of the difference between the input level on CK and the input on \overline{CK} .2. The value of V_{IX} is expected to equal $0.5 \cdot V_{DDQ}$ of the transmitting device and must track variations in the DC level of the same.

10. AC OPERATING TEST CONDITIONS ($V_{DD}=3.3V$, $V_{DDQ}=2.5V$, $T_A=0$ to $70^{\circ}C$)

Parameter	Value	Unit	Note
Input reference voltage for Clock	$0.5 * V_{DDQ}$	V	
Input signal maximum peak swing	1.5	V	
Input signal minimum slew rate	1.0	V/ns	
Input Levels(V_{IH}/V_{IL})	$V_{REF}+0.35/V_{REF}-0.35$	V	
Input timing measurement reference level	V_{REF}	V	
Output timing measurement reference level	V_{tt}	V	
Output load condition	See Load Circuit		



(Fig. 1) Output Load Circuit (SSTL_2)

11. Input/Output CAPACITANCE ($V_{DD}=3.3V$, $V_{DDQ}=2.5V$, $T_A=25^{\circ}C$, $f=1MHz$)

Parameter	Symbol	Min	Max	Unit
Input capacitance($A_0 \sim A_{11}$, $BA_0 \sim BA_1$, \overline{RAS} , \overline{CAS} , \overline{WE})	C_{IN1}	-	50	pF
Input capacitance($\overline{CKE0}$, $\overline{CKE1}$)	C_{IN2}	-	35	pF
Input capacitance($\overline{CS0}$, $\overline{CS1}$)	C_{IN3}	-	32	pF
Input capacitance($\overline{CLK0}$, $\overline{CLK0}$, $\overline{CLK2}$, $\overline{CLK2}$)	C_{IN4}	-	42	pF
Data & DQS input/output capacitance($DQ_0 \sim DQ_{63}$)	C_{OUT}	-	16	pF
Input capacitance($DM_0 \sim DM_8$)	C_{IN5}	-	16	pF

12. AC CHARACTERISTICS. (These AC characteristics were tested on the Component)

Parameter	Symbol	- Z(PC266@CL=2)		- Y(PC266@CL=2.5)		- O(PC200@CL=2)		Unit	Note
		Min	Max	Min	Max	Min	Max		
Row cycle time	tRC	65		65		70		ns	
Refresh row cycle time	tRFC	75		75		80		ns	
Row active time	tRAS	45	12K	48	12K	48	12K	ns	
RAS to CAS delay	tRCD	20		20		20		ns	
Row precharge time	tRP	20		20		20		ns	
Row active to Row active delay	tRRD	15		15		15		ns	
Write recovery time	tWR	2		2		2		tCK	
Last data in to Read command	tCDLR	1		1		1		tCK	
Last data in to Write command	tCDLW	0		0		0		tCK	
Col. address to Col. address delay	tCCD	1		1		1		tCK	
Clock cycle time	CL=2.0	tCK	7.5	15	10	15	10	15	ns
	CL=2.5		7	15	7.5	15	8	15	ns
Clock high level width	tCH	0.45	0.55	0.45	0.55	0.45	0.55	tCK	
Clock low level width	tCL	0.45	0.55	0.45	0.55	0.45	0.55	tCK	
DQS-out access time from CK/CK	tDQSCK	-0.75	+0.75	-0.75	+0.75	-0.8	+0.8	ns	
Output data access time from CK/CK	tAC	-0.75	+0.75	-0.75	+0.75	-0.8	+0.8	ns	
Data strobe edge to output data edge	tDQSQ	-0.5	+0.5	-0.5	+0.5	-0.6	+0.6	ns	
Read Preamble	tRPRE	0.9	1.1	0.9	1.1	0.9	1.1	tCK	
Read Postamble	tRPST	0.4	0.6	0.4	0.6	0.4	0.6	tCK	
Data out high impedance time from CK/CK	tHZQ	-0.75	+0.75	-0.75	+0.75	-0.8	+0.8	ns	2
CK to valid DQS-in	tDQSS	0.75	1.25	0.75	1.25	0.75	1.25	tCK	
DQS-in setup time	tWPRES	0		0		0		ns	3
DQS-in hold time	tWPREH	0.25		0.25		0.25		tCK	
DQS-in high level width	tDQSH	0.4	0.6	0.4	0.6	0.4	0.6	tCK	
DQS-in low level width	tDQSL	0.4	0.6	0.4	0.6	0.4	0.6	tCK	
DQS-in cycle time	tDSC	0.9	1.1	0.9	1.1	0.9	1.1	tCK	
Address and Control Input setup time	tIS	1.1		1.1		1.2		ns	
Address and Control Input hold time	tIH	1.1		1.1		1.2		ns	
Mode register set cycle time	tMRD	15		15		16		ns	
DQ & DM setup time to DQS	tDS	0.5		0.5		0.6		ns	
DQ & DM hold time to DQS	tDH	0.5		0.5		0.6		ns	
DQ & DM input pulse width	tDIPW	1.75		1.75		2		ns	
Power down exit time	tPDEX	10		10		10		ns	
Exit self refresh to write command	tXSW	95				116		ns	

Parameter	Symbol	PC266A		PC266B		PC200		Unit	Note
		Min	Max	Min	Max	Min	Max		
Exit self refresh to bank active command	tXSA	75		75		80		ns	
Exit self refresh to read command	tXSR	200		200		200		Cycle	
Refresh interval time	128Mb	tREF	15.6		15.6		15.6	us	1
Output DQS valid window	tDV	0.35		0.35		0.35		tCK	
DQS write postamble time	tWPST	0.25		0.25		0.25		tCK	4
Auto precharge write recovery + Precharge time	tDAL	35		35		35		ns	

1. Maximum burst refresh of 8
2. tHZQ transitions occurs in the same access time windows as valid data transitions. These parameters are not referenced to a specific voltage level, but specify when the device output is no longer driving.
3. The specific requirement is that DQS be valid(High or Low) on or before this CK edge. The case shown(DQS going from High_Z to logic Low) applies when no writes were previously in progress on the bus. If a previous write was in progress, DQS could be High at this time, depending on tDQSS.
4. The maximum limit for this parameter is not a device limit. The device will operate with a great value for this parameter, but system performance (bus turnaround) will degrade accordingly.

13. SIMPLIFIED TRUTH TABLE

COMMAND			CKEn-1	CKEn	\overline{CS}	\overline{RAS}	\overline{CAS}	\overline{WE}	DM	BA0,1	A10/AP	A11 A9 ~ A0	Note
Register	Extended MRS		H	X	L	L	L	L	X	OP CODE			1, 2
Register	Mode Register Set		H	X	L	L	L	L	X	OP CODE			1, 2
Refresh	Auto Refresh		H	H	L	L	L	H	X	X			3
	Self Refresh	Entry		L									3
		Exit	L	H	L	H	H	X	X			3	
												H	X
Bank Active & Row Addr.			H	X	L	L	H	H	X	V	Row Address		
Read & Column Address	Auto Precharge Disable		H	X	L	H	L	H	X	V	L	Column Address (A0~A7)	4
	Auto Precharge Enable										H		4
Write & Column Address	Auto Precharge Disable		H	X	L	H	L	L	X	V	L	Column Address (A0~A7)	4
	Auto Precharge Enable										H		4, 6
Burst Stop			H	X	L	H	H	L	X	X			7
Precharge	Bank Selection		H	X	L	L	H	L	X	V	L	X	
	All Banks									X	H		5
Active Power Down		Entry	H	L	H	X	X	X	X	X			
					L	V	V	V					
Exit		L	H	X	X	X	X	X	X				
Precharge Power Down Mode		Entry	H	L	H	X	X	X	X	X			
					L	H	H	H					
		Exit	L	H	H	X	X	X	X				
					L	V	V	V					
DM			H	X					V	X		8	
No Operation Command			H	X	H	X	X	X	X	X			
					L	H	H	H					

(V=Valid, X=Don't Care, H=Logic High, L=Logic Low)

Note : 1. OP Code : Operand Code. A0 ~ A11 & BA0 ~ BA1 : Program keys. (@EMRS/MRS)

2. EMRS/ MRS can be issued only at all banks precharge state.

A new command can be issued 2 clock cycles after EMRS or MRS.

3. Auto refresh functions are same as the CBR refresh of DRAM.

The automatical precharge without row precharge command is meant by "Auto".

Auto/self refresh can be issued only at all banks precharge state.

4. BA0 ~ BA1 : Bank select addresses.

If both BA0 and BA1 are "Low" at read, write, row active and precharge, bank A is selected.

If both BA0 is "High" and BA1 is "Low" at read, write, row active and precharge, bank B is selected.

If both BA0 is "Low" and BA1 is "High" at read, write, row active and precharge, bank C is selected.

If both BA0 and BA1 are "High" at read, write, row active and precharge, bank D is selected.

5. If A10/AP is "High" at row precharge, BA0 and BA1 are ignored and all banks are selected.

6. During burst write with auto precharge, new read/write command can not be issued.

Another bank read/write command can be issued after the end of burst.

New row active of the associated bank can be issued at tRP after the end of burst.

7. Burst stop command is valid at every burst length.

8. DM sampled at the rising and falling edges of the DQS and Data-in are masked at the both edges (Write DM latency is 0).

184pin Unbuffered DDR SDRAM MODULE Preliminary

Units : Inches (Millimeters)

